

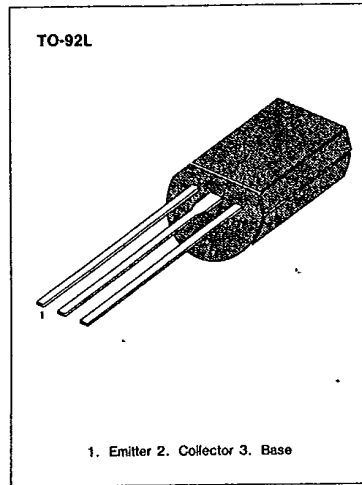
KSC2383

NPN EPITAXIAL SILICON TRANSISTOR

COLOR TV AUDIO OUTPUT
 COLOR TV VERTICAL DEFLECTION OUTPUT

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	160	V
Collector-Emitter Voltage	V _{CE0}	160	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	I _C	1	A
Base Current	I _B	0.5	A
Collector Dissipation	P _C	900	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

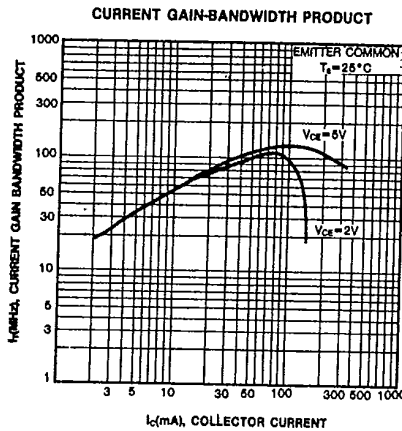
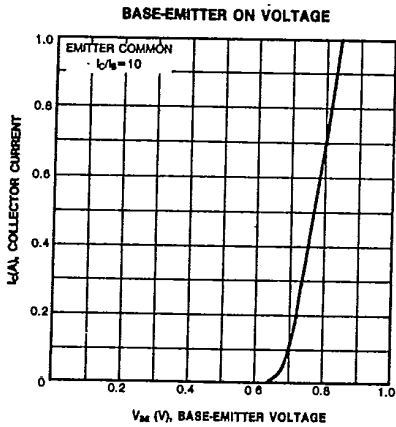
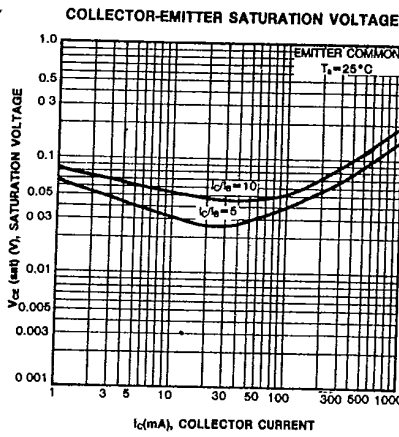
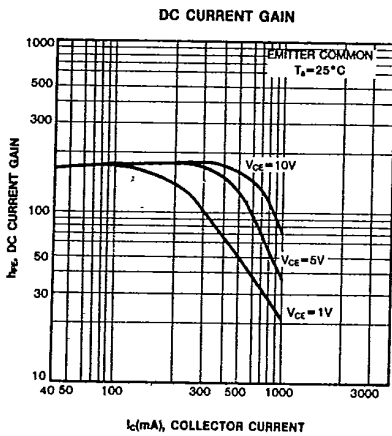
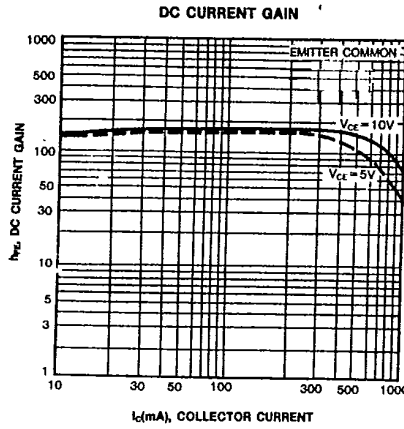
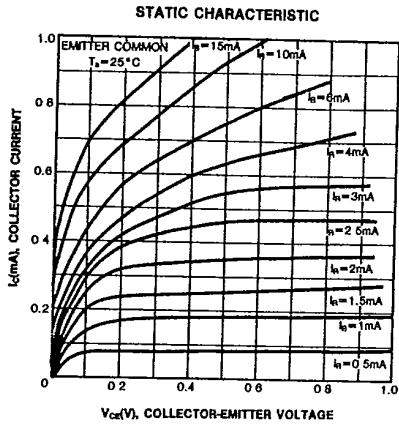
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} =150V, I _E =0			1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =6V, I _C =0			1	μA
Collector-Emitter Breakdown Voltage	BV _{CE0}	I _C =10mA, I _B =0	.160			V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =200mA	60		320	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C =500mA, I _B =50mA			1.5	V
Base Emitter On Voltage	V _{BE (on)}	V _{CE} =5V, I _C =5mA	0.45		0.75	V
Current Gain-Bandwidth Product	f _T	V _{CE} =5V, I _C =200mA	20	100		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			20	pF

h_{FE} CLASSIFICATION

Classification	R	O	Y
h _{FE}	60-120	100-200	160-320

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